SKT 551



Capsule Thyristors

Thyristors

SKT 551

Features

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- Shallow design with single sided cooling
- · International standard case
- Off-state and reverse voltages up to 1800 V
- · Amplifying gate

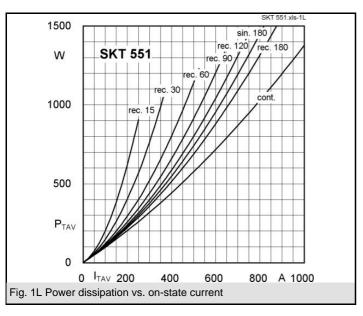
Typical Applications

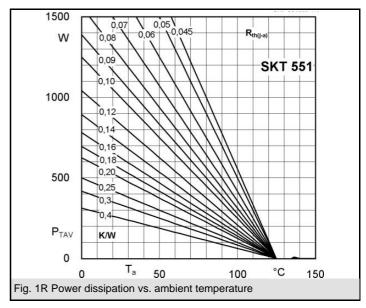
- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers
 - (e. g. for temperature control)
- Recommended snubber network e.g. for $V_{VRMS} \le 400 \text{ V}$: R = 33 $\Omega/32$ W, C = 0,47 μF

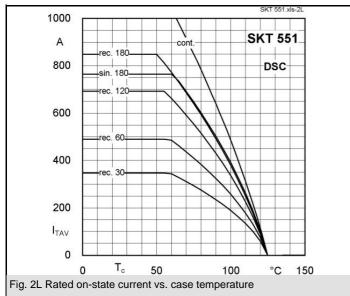
V _{RSM}	V _{RRM} , V _{DRM}	I _{TRMS} = 1200 A (maximum value for continuous operation)	
V	V	I _{TAV} = 550 A (sin. 180; DSC; T _c = 85 °C)	
900	800	SKT 551/08E	
1300	1200	SKT 551/12E	
1500	1400	SKT 551/14E	
1700	1600	SKT 551/16E	
1900	1800	SKT 551/18E	

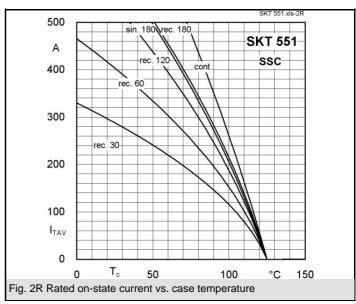
Symbol	Conditions	Values	Units
I _{TAV}	sin. 180; T _c = 100 (85) °C;	391 (550)	Α
I _D	2 x P8/180; T _a = 45 °C; B2 / B6	390 / 560	Α
	2 x P8/180 F; T _a = 35 °C; B2 / B6	980 /1340	Α
I _{RMS}	2 x P8/180; T _a = 45 °C; W1C	430	Α
I _{TSM}	T _{vj} = 25 °C; 10 ms	9000	Α
	$T_{vj} = 125 ^{\circ}\text{C}; 10 \text{ms}$	8000	Α
i²t	$T_{vj} = 25 ^{\circ}\text{C}; 8,3 \dots 10 \text{ms}$	405000	A²s
	T _{vj} = 125 °C; 8,3 10 ms	320000	A²s
V _T	T _{vi} = 25 °C; I _T = 1500 A	max. 1,65	V
$V_{T(TO)}$	T _{vi} = 125 °C	max. 0,925	V
r _T	T _{vj} = 125 °C	max. 0,45	mΩ
I _{DD} ; I _{RD}	$T_{vj} = 125 ^{\circ}\text{C}; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 50	mA
t _{gd}	$T_{vj} = 25 ^{\circ}\text{C}; I_{G} = 1 \text{A}; di_{G}/dt = 1 \text{A/}\mu\text{s}$	1	μs
t _{gr}	$V_{\rm D} = 0.67 * V_{\rm DRM}$	1	μs
(di/dt) _{cr}	T _{vi} = 125 °C	max. 125	A/µs
(dv/dt) _{cr}	T _{vi} = 125 °C	max. 1000	V/µs
t _q	T _{vj} = 125 °C	50 150	μs
I _H	$T_{vj} = 25 ^{\circ}\text{C}$; typ. / max.	150 / 500	mA
IL	T_{vj} = 25 °C; R_G = 33 Ω ; typ. / max.	500 / 2000	mA
V _{GT}	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 3	V
I _{GT}	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 250	mA
V_{GD}	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	max. 10	mA
R _{th(j-c)}	cont.; DSC	0,045	K/W
R _{th(j-c)}	sin. 180; DSC / SSC	0,047 / 0,1	K/W
$R_{th(j-c)}$	rec. 120; DSC / SSC	0,054 / 0,113	K/W
R _{th(c-s)}	DSC / SSC	0,012 / 0,024	K/W
T_{vj}		- 40 + 125	°C
T_{stg}		- 40 + 130	°C
V _{isol}		-	V~
F	mounting force	5,2 8	kN
а			m/s²
m	approx.	105	g
Case		B 11	

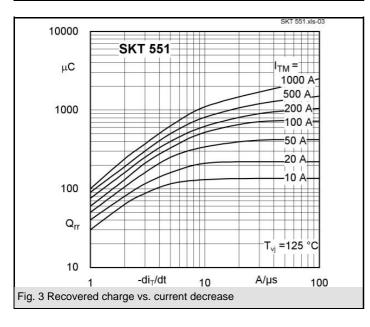


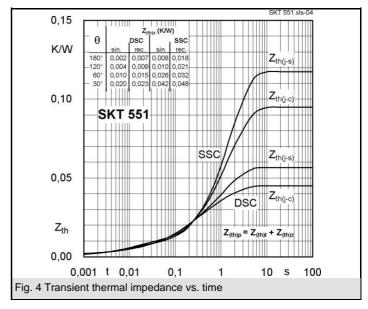




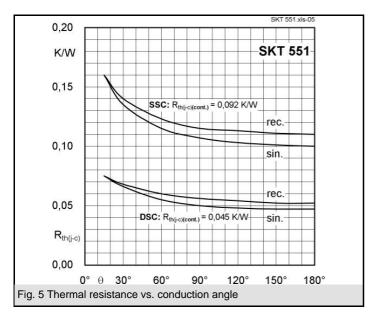


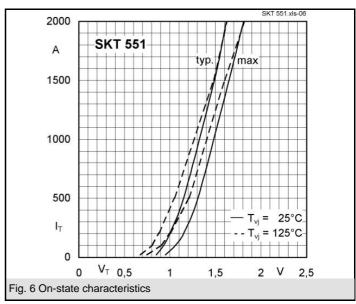


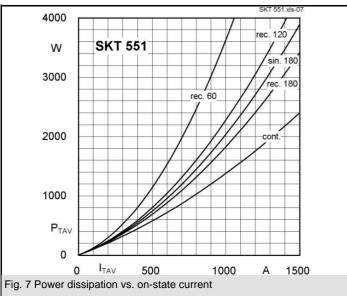


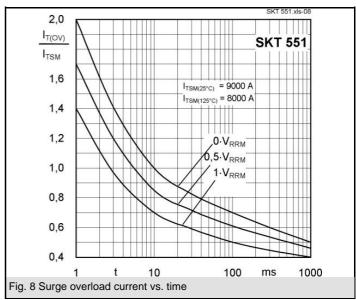


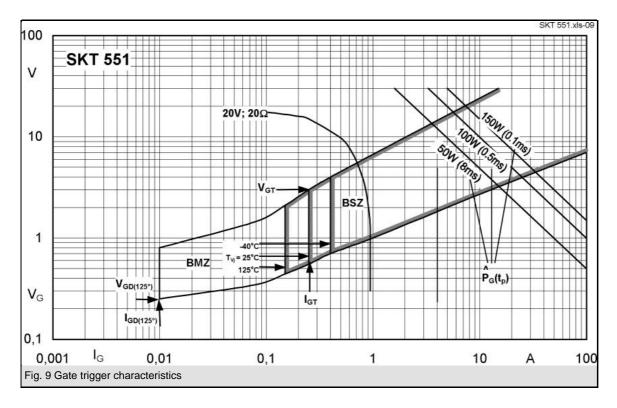
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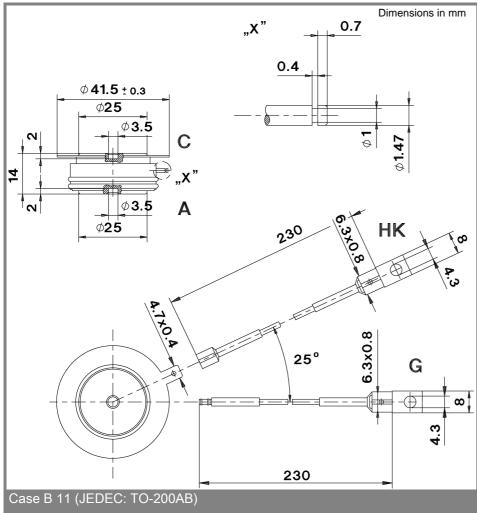












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